

Features

- Split Gate Trench MOSFET Technology
- Low R_{DS(on)} & FOM
- Low Crss
- · ExtremelyLow Switching Loss
- · Excellent Stability and Uniformity
- · Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- Moisture Sensitivity Level 1

Maximum Ratings

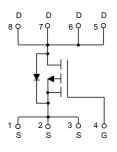
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 20°C/W Junction to Ambient(t≤10s)⁽²⁾
- Thermal Resistance: 50°C/W Junction to Ambient(Steady-State) (2)
- Thermal Resistance: 2.1°C/W Junction to Case(Steady-State)

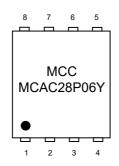
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Volltage	V_{GS}	±20	V
Continuous Drain Current	I _D	-28	Α
Pulsed Drain Current (3)	I _{DM}	-86	Α
Total Power Dissipation ⁽⁴⁾	P _D	60	W
Single Pulsed Avalanche Energy ⁽⁵⁾	E _{AS}	81	mJ

Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of $R_{\theta JA}$ is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation PDSM is based on $R_{\theta JA}$ t ≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. Pd is based on max. junction temperature, using junction-case thermal resistance.
- 5. V_{DD} =50V, R_{G} =25 Ω , L=0.5mH, I_{AS} =25A.

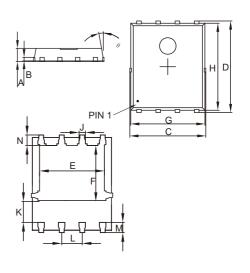
Internal Structure and Marking Code





P-CHANNEL MOSFET

DFN5060



DIMENSIONS					
DIM INCHES		MM		NOTE	
Dilvi	MIN	MAX	MIN	MAX	NOIL
Α	0.031	0.047	0.80	1.20	
В	0.010		0.010 0.254		TYP.
С	0.193	0.222	4.90	5.64	
D	0.232	0.250	5.90	6.35	
E	0.148	0.167	3.75	4.25	
F	0.126	0.154	3.20	3.92	
G	0.189	0.213	4.80	5.40	
Н	0.222	0.239	5.65	6.06	
K	0.045	0.059	1.15	1.50	
J	0.012	0.020	0.30	0.50	
L	0.046	0.054	1.17	1.37	
M	0.012	0.028	0.30	0.71	
N	0.016	0.028	0.40	0.71	

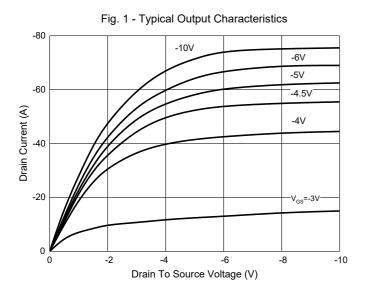


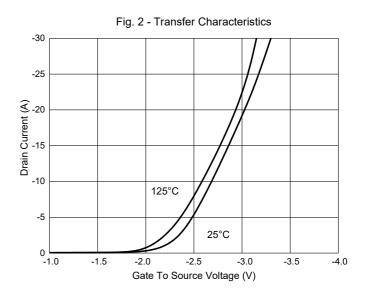
Electrical Characteristics @ 25°C (Unless Otherwise Specified)

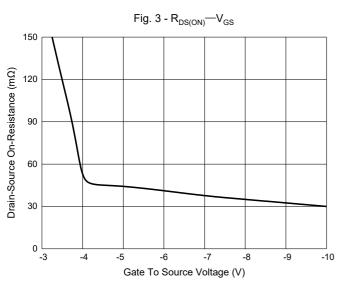
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250µA	-60			V	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V			-1	μA	
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.5	-2.1	-2.7	V	
Dunin Course On Braintan		V _{GS} =-10V, I _D =-20A		30	40	mΩ	
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-10A		41	55	mΩ	
Diode Characteristics					1		
Continuous Body Diode Current	Is				-28	Α	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-20A			-1.3	V	
Reverse Recovery Time	t _{rr}	1 004 11/11 4004/		19		ns	
Reverse Recovery Charge	Q _{rr}	I _S =-20A,di/dt=100A/μs		3.9		nC	
Dynamic Characteristics					•		
Input Capacitance	C _{iss}			1050			
Output Capacitance	C _{oss}	V _{DS} =-30V,V _{GS} =0V,f=1MHz		340		pF	
Reverse Transfer Capacitance	C _{rss}			62		1	
Total Gate Charge	Q_g			19.3			
Gate-Source Charge	Q _{gs}	V _{DS} =-30V,V _{GS} =-10V,I _D =-20A		5.3		nC	
Gate-Drain Charge	Q_{gd}			3.1			
Turn-On Delay Time	t _{d(on)}			6			
Turn-On Rise Time	t _r	V _{DS} =-30V, V _{GS} =-10V,		45.6			
Turn-Off Delay Time	t _{d(off)}	$R_G=6\Omega$, $R_L=2.5\Omega$		42.8		ns	
Turn-Off Fall Time	t _f			75.6			

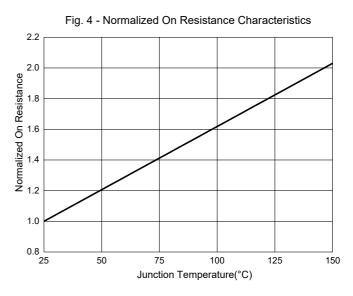


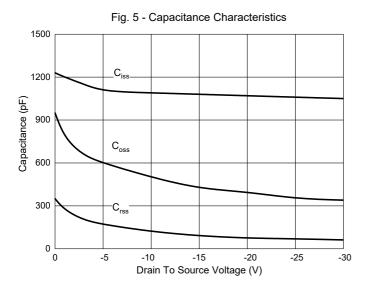
Curve Characteristics

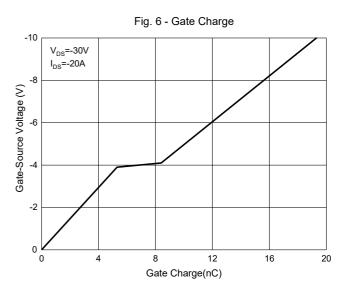














Curve Characteristics

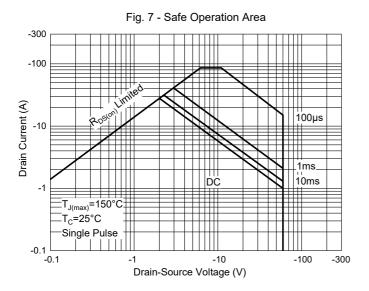
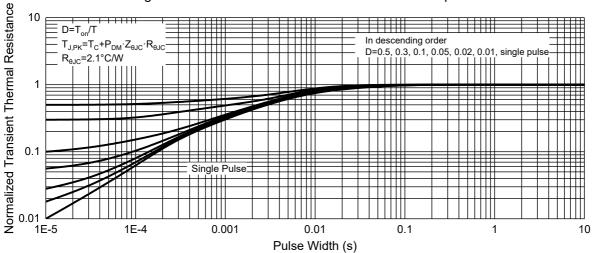


Fig. 8 - Normalized Maximum Transient Thermal Impedance





Ordering Information

Device	Packing	
Part Number-TP	Tape&Reel: 5Kpcs/Reel	

IMPORTANT NOTICE

Micro Commercial Components Corp. reserves the right to make changes without further notice to any product herein to make corrections, modifications, enhancements, improvements, or other changes. **Micro Commercial Components Corp.** does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold **Micro Commercial Components Corp.** and all the companies whose products are represented on our website, harmless against all damages. **Micro Commercial Components Corp.** products are sold subject to the general terms and conditions of commercial sale, as published at

https://www.mccsemi.com/Home/TermsAndConditions.

LIFE SUPPORT

MCC's products are not authorized for use as critical components in life support devices or systems without the express written approval of Micro Commercial Components Corporation.

CUSTOMER AWARENESS

Counterfeiting of semiconductor parts is a growing problem in the industry. Micro Commercial Components (MCC) is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. MCC strongly encourages customers to purchase MCC parts either directly from MCC or from Authorized MCC Distributors who are listed by country on our web page cited below. Products customers buy either from MCC directly or from Authorized MCC Distributors are genuine parts, have full traceability, meet MCC's quality standards for handling and storage. MCC will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. MCC is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

单击下面可查看定价,库存,交付和生命周期等信息

>>MCC(美微科)